

## AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Currently amended) A negative type photosensitive resin

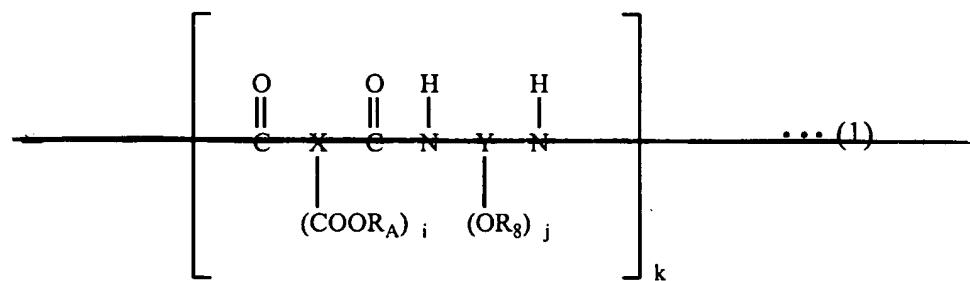
composition which comprises:

(A) 100 parts of a polyamide having a structural unit represented by the following formula (1) and having a photopolymerizable unsaturated double bond: ~~100 parts by mass,~~

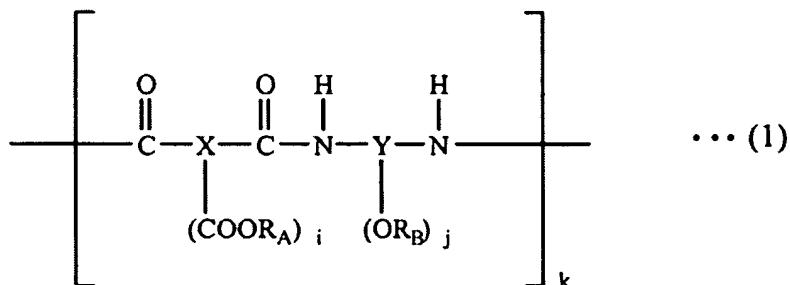
(B) 1-50 parts of a monomer having a photopolymerizable unsaturated double bond: ~~1-50 parts by mass,~~

(C) 1-20 parts of a photopolymerization initiator: ~~1-20 parts by mass~~, and

(D) 5-30 parts of a melamine resin: ~~5-30 parts by mass~~,

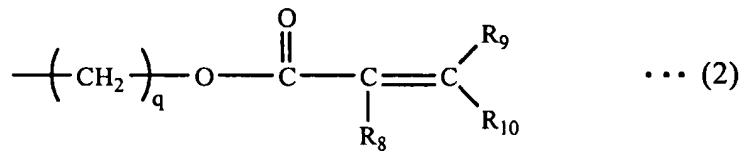


... (1)

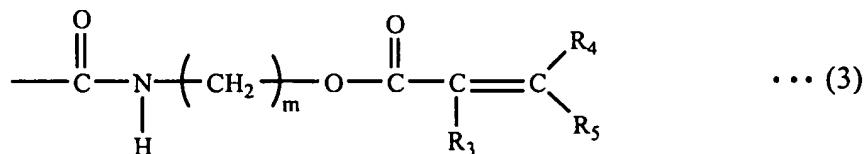


... (1)

(where X is a 2-4 valent aromatic group and Y is a 2-4 valent aromatic group, i and j are integers of 0-2 and satisfy  $i + j = 2$ , k is an integer of 2-150,  $R_A$  is independently a monovalent organic group having a photopolymerizable unsaturated double bond and represented by the following formula (2) or a saturated aliphatic group of 1-4 carbon atoms, and  $R_B$  is independently a hydrogen atom or a monovalent organic group having a photopolymerizable unsaturated double bond and represented by the following formula (3), with the proviso that when the total mol number of  $R_B$  is assumed to be 100 mol%, not less than 10 mol% and not more than 50 mol% thereof is the monovalent organic group having a photopolymerizable unsaturated double bond and represented by the following formula (3),



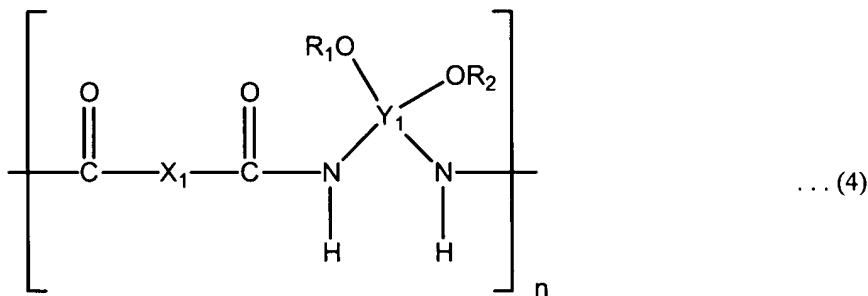
where  $R_8$  is a hydrogen atom or an organic group of 1-3 carbon atoms,  $R_9$  and  $R_{10}$  are independently a hydrogen atom or an organic group of 1-3 carbon atoms, and  $q$  is an integer of 2-10,



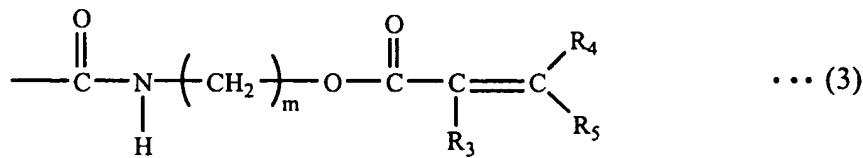
where  $R_3$  is a hydrogen atom or an organic group of 1-3 carbon atoms,  $R_4$  and  $R_5$  are independently a hydrogen atom or an organic group of 1-3 carbon atoms, and  $m$  is an integer of 2-10).

2. (Original) A negative type photosensitive resin composition according to claim 1, wherein the polyamide (A) having a photopolymerizable unsaturated double

bond is a polybenzoxazole precursor having a structural unit represented by the following formula (4):



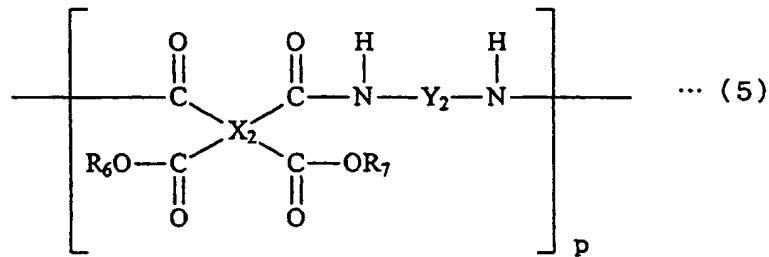
(where  $X_1$  is a divalent aromatic group,  $Y_1$  is a tetravalent aromatic group,  $n$  is an integer of 2-150, and  $R_1$  and  $R_2$  are independently a hydrogen atom or a monovalent organic group having a photopolymerizable unsaturated double bond and represented by the following formula (3), with the proviso that when the total mol of  $R_1$  and  $R_2$  is assumed to be 100 mol%, not less than 10 mol% and not more than 50 mol% of  $R_1$  and  $R_2$  are the monovalent organic groups having a photopolymerizable unsaturated double bond and represented by the following formula (3):



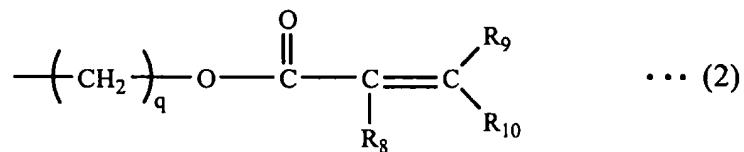
where  $R_3$  is a hydrogen atom or an organic group of 1-3 carbon atoms,  $R_4$  and  $R_5$  are independently a hydrogen atom or an organic group of 1-3 carbon atoms, and  $m$  is an integer of 2-10).

3. (Original) A negative type photosensitive resin composition according to claim 1, wherein the polyamide (A) having a photopolymerizable unsaturated double

bond is a polyimide precursor having a structural unit represented by the following formula (5):



(where  $\text{X}_2$  is a tetravalent aromatic group, and the  $-\text{COOR}_6$  group and the  $-\text{COOR}_7$  group, and the  $-\text{CONH}-$  group adjacent thereto are in the ortho position to each other,  $\text{Y}_2$  is a divalent aromatic group,  $p$  is an integer of 2-150, and  $\text{R}_6$  and  $\text{R}_7$  are independently a monovalent organic group having a photopolymerizable unsaturated double bond and represented by the following formula (2) or a saturated aliphatic group of 1-4 carbon atoms:



where  $\text{R}_8$  is a hydrogen atom or an organic group of 1-3 carbon atoms,  $\text{R}_9$  and  $\text{R}_{10}$  are independently a hydrogen atom or an organic group of 1-3 carbon atoms, and  $q$  is an integer of 2-10).

4. (Original) A negative type photosensitive resin composition according to any one of claims 1-3, wherein the melamine resin (D) has a polymerization degree of not less than 1.0 and not more than 2.2.

5. (Original) A negative type photosensitive resin composition according to any one of claims 1-3, wherein the melamine resin (D) is a hexamethoxymethylated melamine.

6. (Previously presented) A method for forming a heat resistant and chemical resistant relief pattern which comprises:

- (1) coating the negative type photosensitive resin composition according to any one of claims 1-3 on a substrate,
- (2) subjecting the coating to exposure by irradiating with active rays through a patterning mask,
- (3) dissolving and removing the unexposed portions of the coating using a developer to form a relief pattern, and
- (4) heating the coating at a temperature of not lower than 200°C to cure the coating.

7. (Original) A method for producing a semiconductor device which includes forming a relief pattern by the relief pattern forming method according to claim 6.

8. (Cancelled)

9. (Previously presented) A method for forming a heat resistant and chemical resistant relief pattern which comprises:

- (1) coating the negative type photosensitive resin composition according to claim 4 on a substrate,
- (2) subjecting the coating to exposure by irradiating with active rays through a patterning mask,
- (3) dissolving and removing the unexposed portions of the coating using a developer to form a relief pattern, and
- (4) heating the coating at a temperature of not lower than 200°C to cure the coating.

10. (Previously presented) A method for producing a semiconductor device which includes forming a relief pattern by the relief pattern forming method according to claim 9.

11. (Previously presented) A method for forming a heat resistant and chemical resistant relief pattern which comprises:

- (1) coating the negative type photosensitive resin composition according to claim 5 on a substrate,
- (2) subjecting the coating to exposure by irradiating with active rays through a patterning mask,
- (3) dissolving and removing the unexposed portions of the coating using a developer to form a relief pattern, and
- (4) heating the coating at a temperature of not lower than 200°C to cure the coating.

12. (Previously presented) A method for producing a semiconductor device which includes forming a relief pattern by the relief pattern forming method according to claim 11.